

N-Channel Silicon Junction Field-Effect Transistor

• Low-Noise, High Gain Amplifier

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Reverse Gate Drain Voltage	- 20 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	225 mW
Power Derating	1.8 mW/°C
Storage Temperature Range	- 65°C to 200°C

At 25°C free air temperature:

Static Electrical Characteristics

		IF1330		Process NJ132H		
		Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 20		V	$I_G = - 1 \mu\text{A}, V_{DS} = \emptyset\text{V}$	
Gate Reverse Current	I_{GSS}		- 0.1	nA	$V_{DS} = \emptyset\text{V}, V_{GS} = - 10\text{V}$	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 0.35	- 1.5	V	$V_{DS} = 10\text{V}, I_D = 0.5 \text{ mA}$	
Drain Saturation Current (Pulsed)	I_{DSS}	5	20	mA	$V_{DS} = 10\text{V}, V_{GS} = \emptyset\text{V}$	

Dynamic Electrical Characteristics

Common Source Forward Transconductance	g_{fs}	10		mS	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$	$f = 1 \text{ kHz}$
Common Source Input Capacitance	C_{iss}		20	pF	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$	$f = 1 \text{ MHz}$
Common Source Reverse Transfer Capacitance	C_{rss}		5	pF	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$	$f = 1 \text{ MHz}$

Typ

Equivalent Short Circuit Input Noise Voltage	\bar{e}_N	2.5		nV/√Hz	$V_{DS} = 10\text{V}, I_D = 5 \text{ mA}$	$f = 1 \text{ kHz}$
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TO-236AB Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate